

AO4476
N-Channel Enhancement Mode Field Effect Transistor

General Description

The AO4476/L uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. This device is suitable for use as a high side switch in SMPS and general purpose applications.

AO4476 and AO4476L are electrically identical.

-RoHS Compliant

-AO4476L is Halogen Free

Features

V_{DS} (V) = 30V

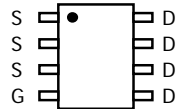
I_D = 15A (V_{GS} = 10V)

$R_{DS(ON)} < 10.5m\Omega$ (V_{GS} = 10V)

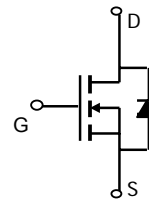
$R_{DS(ON)} < 17m\Omega$ (V_{GS} = 4.5V)

UIS Tested

Rg, Ciss, Coss, Crss Tested



SOIC-8


Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^{AF}	$T_A=25^\circ\text{C}$	15	A
	$T_A=70^\circ\text{C}$	12	
Pulsed Drain Current ^B	I_{DM}	60	
Power Dissipation	$T_A=25^\circ\text{C}$	3.7	W
	$T_A=70^\circ\text{C}$	2.4	
Avalanche Current ^B	I_{AR}	30	A
Repetitive avalanche energy 0.3mH ^B	E_{AR}	135	mJ
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	28	34	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A		Steady-State	57	71
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	16	23	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±20V			0.1	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1	2.1	2.5	V
I _{D(ON)}	On state drain current	V _{GS} =10V, V _{DS} =5V	60			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =15A T _J =125°C		8.5 11	10.5	mΩ
		V _{GS} =4.5V, I _D =12A		14	17	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =15A		33		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.73	1.0	V
I _S	Maximum Body-Diode Continuous Current				5	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance			1000	1200	pF
C _{oss}	Output Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		340	408	pF
C _{rss}	Reverse Transfer Capacitance			100	140	pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	0.6	1.3	2.0	Ω
SWITCHING PARAMETERS						
Q _{g(10V)}	Total Gate Charge			18	23	nC
Q _{g(4.5V)}	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =15A		8.5	11	nC
Q _{gs}	Gate Source Charge			3.1		nC
Q _{gd}	Gate Drain Charge			4.8		nC
t _{D(on)}	Turn-On Delay Time			6		ns
t _r	Turn-On Rise Time	V _{GS} =10V, V _{DS} =15V, R _L =1Ω,		3.8		ns
t _{D(off)}	Turn-Off Delay Time	R _{GEN} =3Ω		20		ns
t _f	Turn-Off Fall Time			3.8		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =15A, dI/dt=100A/μs		28	34	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =15A, dI/dt=100A/μs		21		nC

A: The value of R_{θJA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_J=25°C. The SOA curve provides a single pulse rating.

F: The current rating is based on the ≤ 10s junction to ambient thermal resistance rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

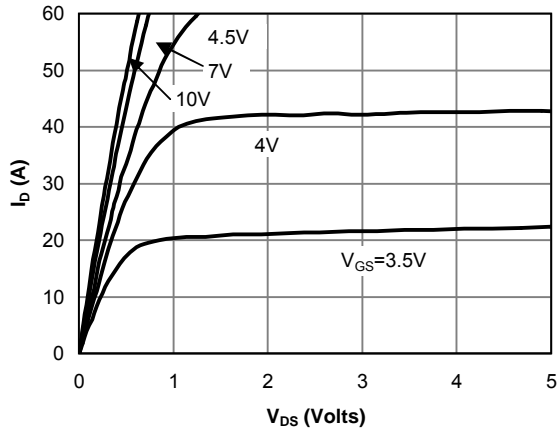


Figure 1: On-Region Characteristics

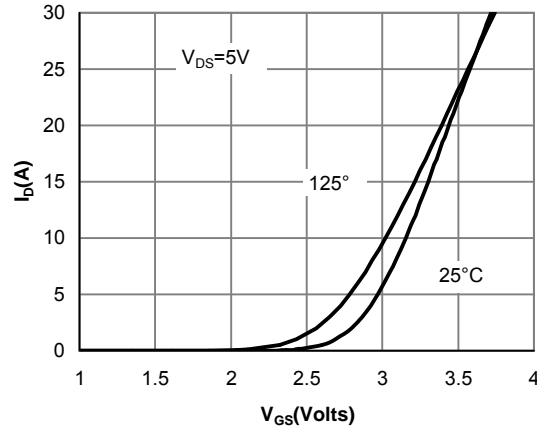


Figure 2: Transfer Characteristics

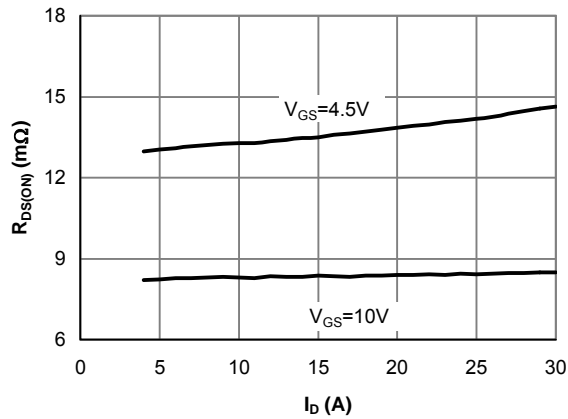


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

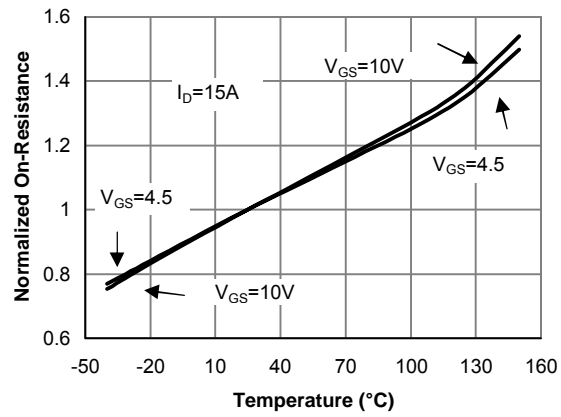


Figure 4: On-Resistance vs. Junction Temperature

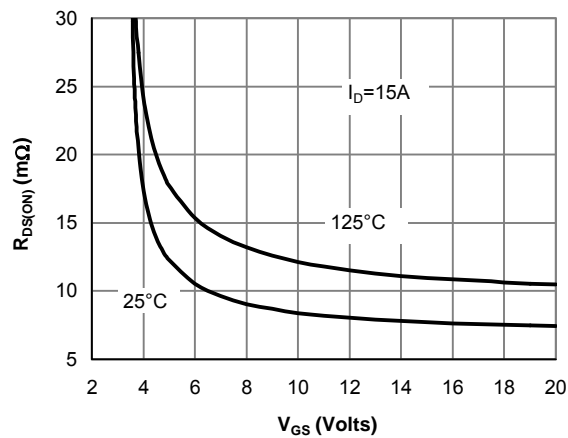


Figure 5: On-Resistance vs. Gate-Source Voltage

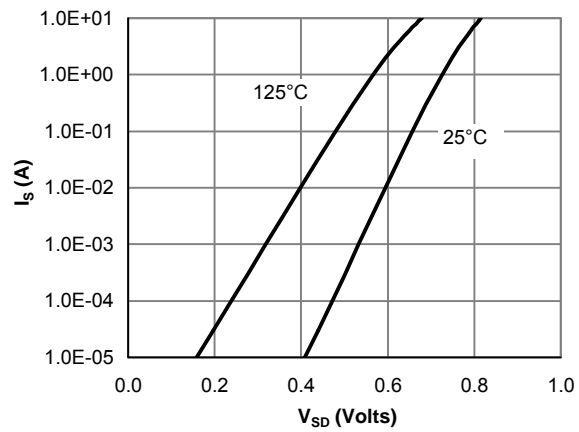


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

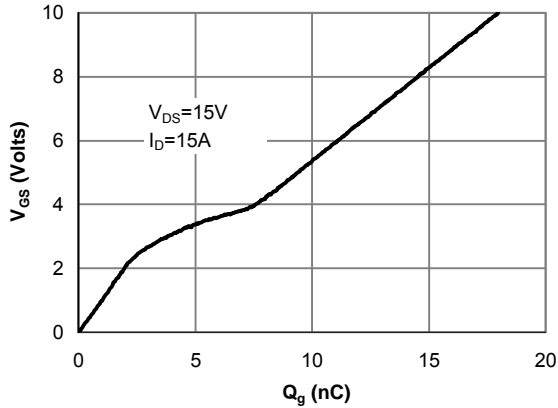


Figure 7: Gate-Charge Characteristics

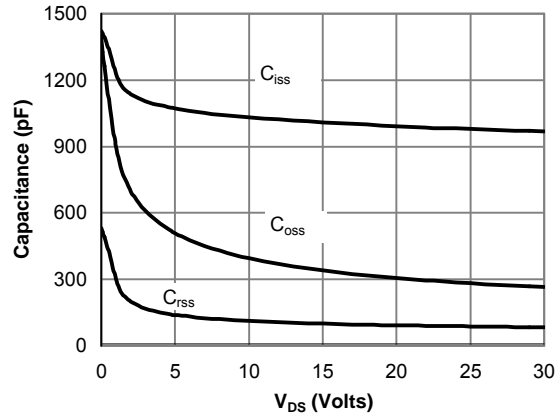


Figure 8: Capacitance Characteristics

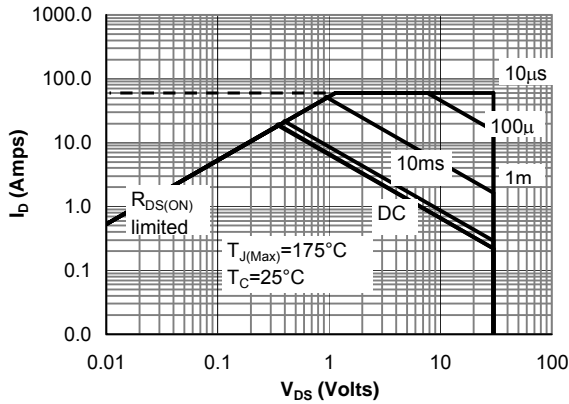


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

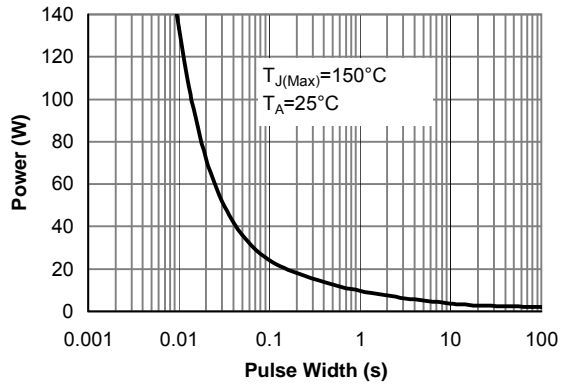


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note G)

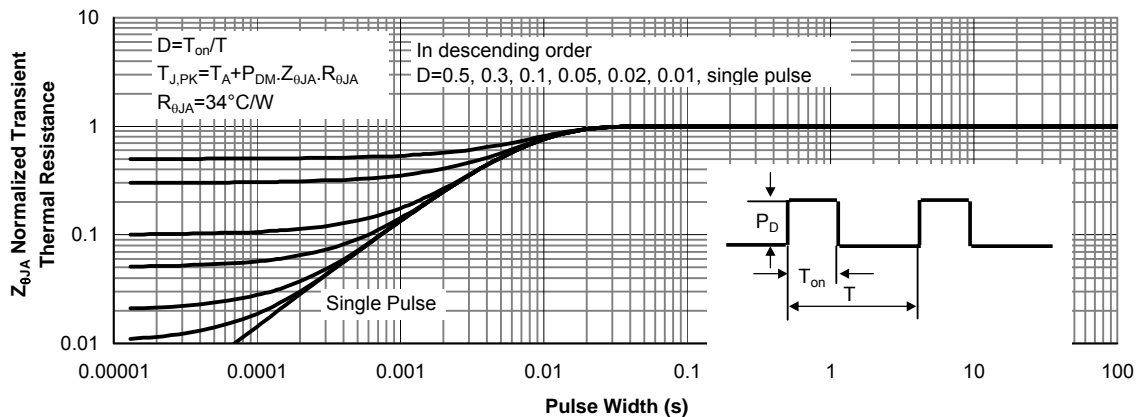


Figure 11: Normalized Maximum Transient Thermal Impedance (Note G)